

# International Rectifier

HEXFRED™

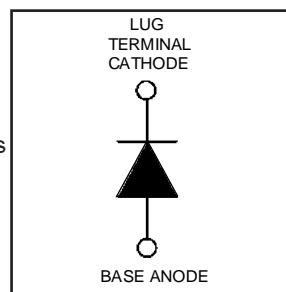
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## HFA180NH40R

Ultrafast, Soft Recovery Diode

### Features

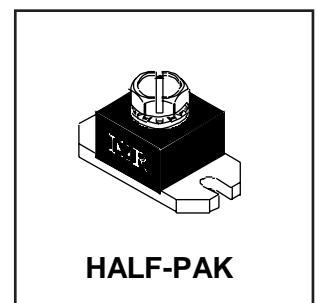
- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters



$V_R = 400V$
$V_F(\text{typ.})^{\circledcirc} = 1.1V$
$I_F(\text{AV}) = 180A$
$Q_{rr} (\text{typ.}) = 420nC$
$I_{RRM}(\text{typ.}) = 8.7A$
$t_{rr}(\text{typ.}) = 45ns$
$di_{(\text{rec})M}/dt (\text{typ.})^{\circledcirc} = 280A/\mu s$

### Description

HEXFRED™ diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and  $di/dt$  simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.



### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_R$	Cathode-to-Anode Voltage	400	V
$I_F @ T_C = 25^\circ C$	Continuous Forward Current	280	
$I_F @ T_C = 100^\circ C$	Continuous Forward Current	138	
$I_{FSM}$	Single Pulse Forward Current ①	1200	A
$I_{AS}$	Maximum Single Pulse Avalanche Current ②	5.0	
$E_{AS}$	Non-Repetitive Avalanche Energy ③	1.4	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	521	
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	208	W
$T_J$	Operating Junction and Storage Temperature Range	-55 to +150	°C

### Thermal - Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.24	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat , Greased Surface	—	0.15	—	K/W
Wt	Weight	—	26 (0.9)	—	g (oz)
	Mounting Torque	15 (1.7)	—	25 (2.8)	lbf-in
	Terminal Torque	20 (2.2)	—	40 (4.4)	(N•m)

**Note:** ① Limited by junction temperature  
 ②  $L = 100\mu H$ , duty cycle limited by max  $T_J$   
 ③  $125^\circ C$

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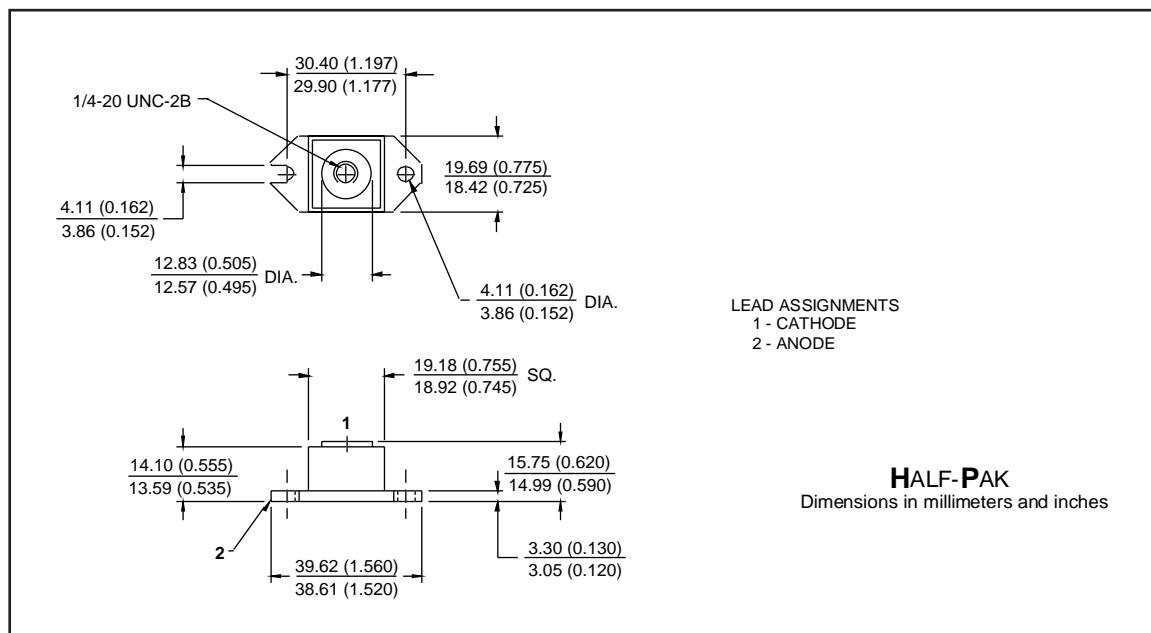
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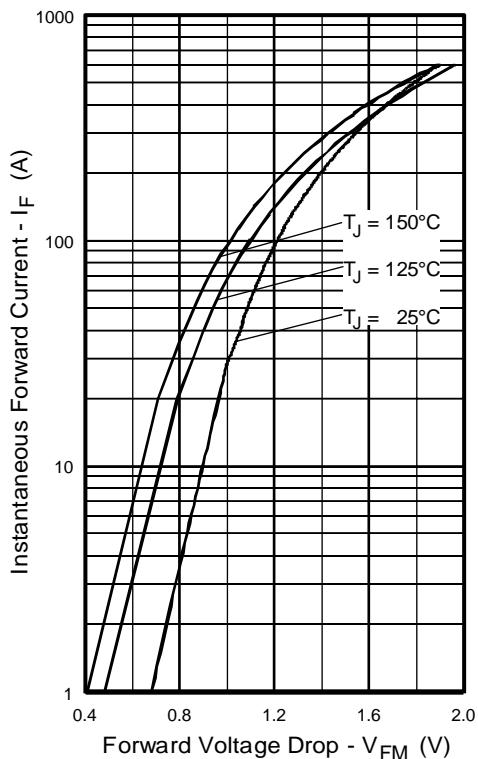
## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{BR}$	Cathode Anode Breakdown Voltage	400	—	—	V	$I_R = 100\mu\text{A}$
$V_{FM}$	Max Forward Voltage	—	1.10	1.35	V	$I_F = 180\text{A}$
		—	1.40	1.65		$I_F = 360\text{A}$
		—	1.10	1.30		$I_F = 180\text{A}, T_J = 125^\circ\text{C}$
$I_{RM}$	Max Reverse Leakage Current	—	2.0	12	$\mu\text{A}$	$V_R = V_R$ Rated
		—	3.0	16	mA	$T_J = 125^\circ\text{C}, V_R = 320\text{V}$
$C_T$	Junction Capacitance	—	370	500	pF	$V_R = 200\text{V}$
$L_S$	Series Inductance	—	5.0	—	nH	From top of terminal hole to mounting plane

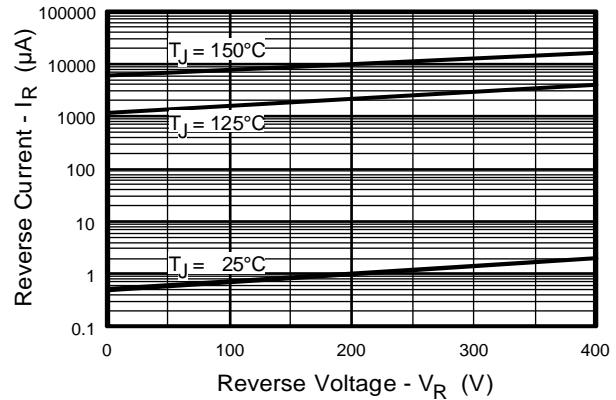
## Dynamic Recovery Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$t_{rr}$	Reverse Recovery Time	—	45	—	ns	$I_F = 1.0\text{A}, dI/dt = 200\text{A}/\mu\text{s}, V_R = 30\text{V}$
		—	90	140		$T_J = 25^\circ\text{C}$ See Fig. 5
		—	290	440		$T_J = 125^\circ\text{C}$ 5
$I_{RRM1}$	Peak Recovery Current	—	8.7	20	A	$T_J = 25^\circ\text{C}$ See Fig. 6
		—	18	30		$T_J = 125^\circ\text{C}$ 6
$Q_{rr1}$	Reverse Recovery Charge	—	420	1100	nC	$T_J = 25^\circ\text{C}$ See Fig. 7
		—	2600	7000		$T_J = 125^\circ\text{C}$ 7
$dI_{(rec)M}/dt_1$	Peak Rate of Fall of Recovery Current During $t_b$	—	300	—	A/ $\mu\text{s}$	$T_J = 25^\circ\text{C}$ See Fig. 8
		—	280	—		$T_J = 125^\circ\text{C}$ 8

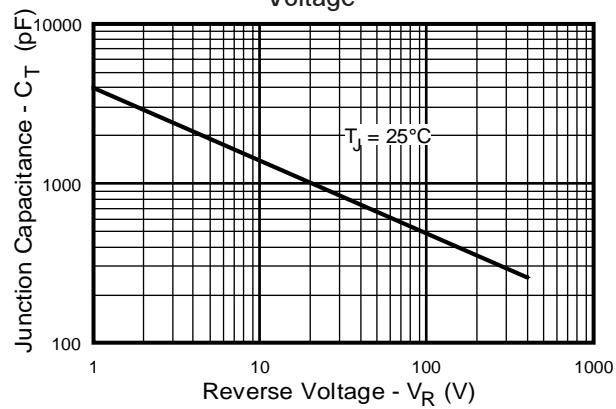




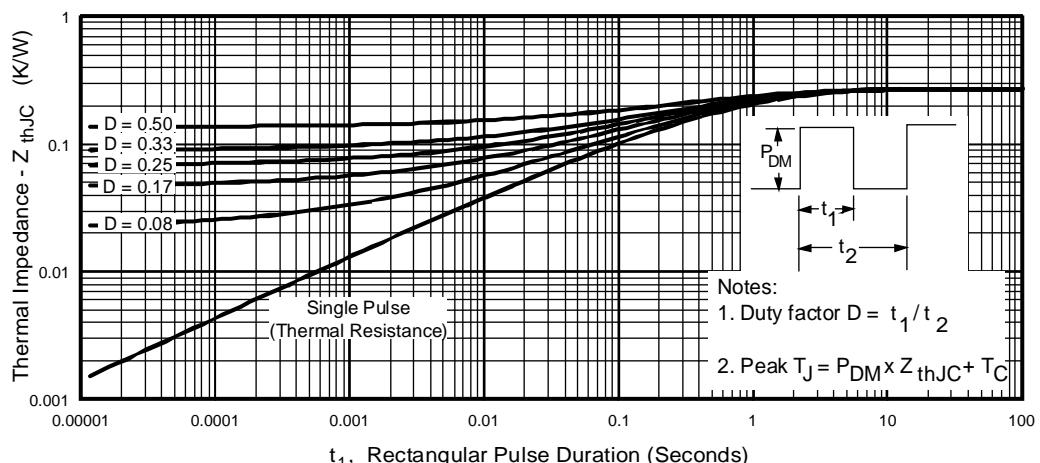
**Fig. 1** - Maximum Forward Voltage Drop vs. Instantaneous Forward Current



**Fig. 2** - Typical Reverse Current vs. Reverse Voltage



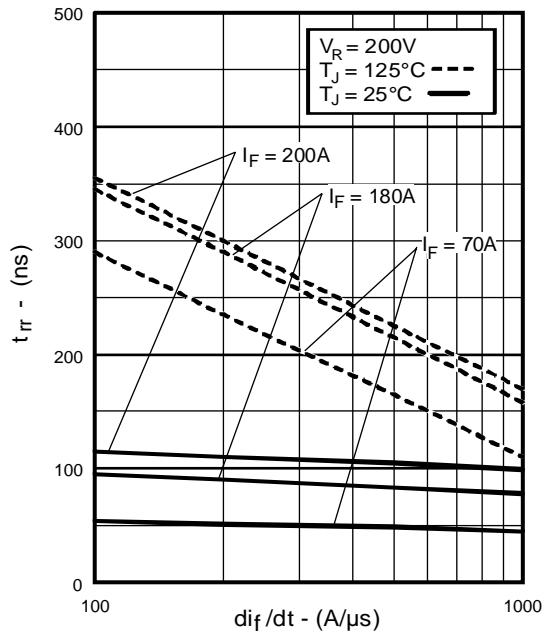
**Fig. 3** - Typical Junction Capacitance vs. Reverse Voltage



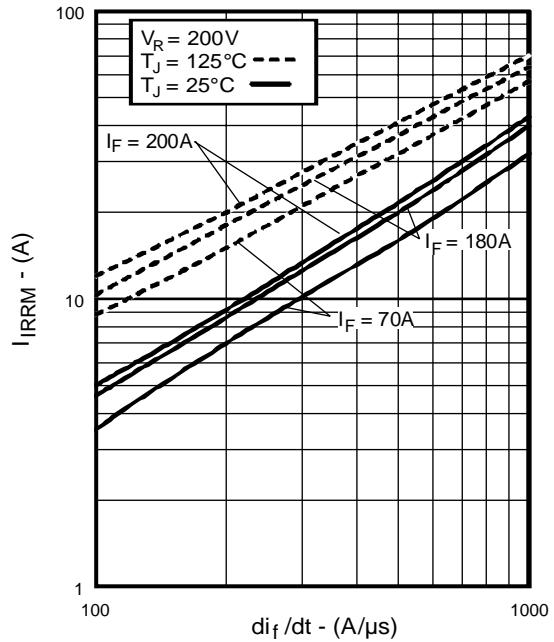
**Fig. 4** - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

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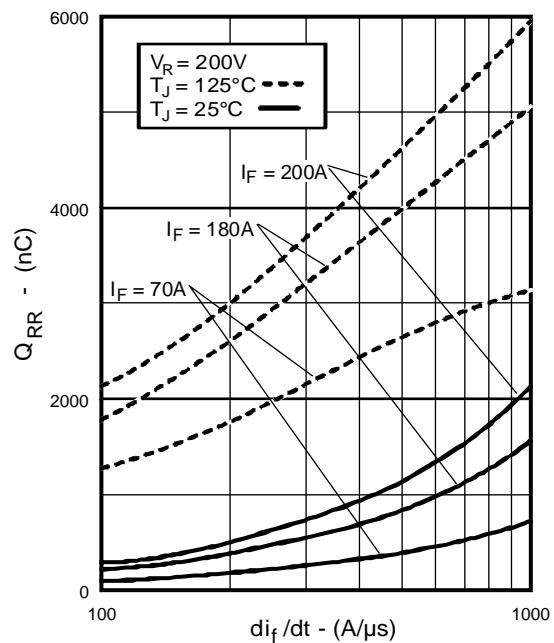
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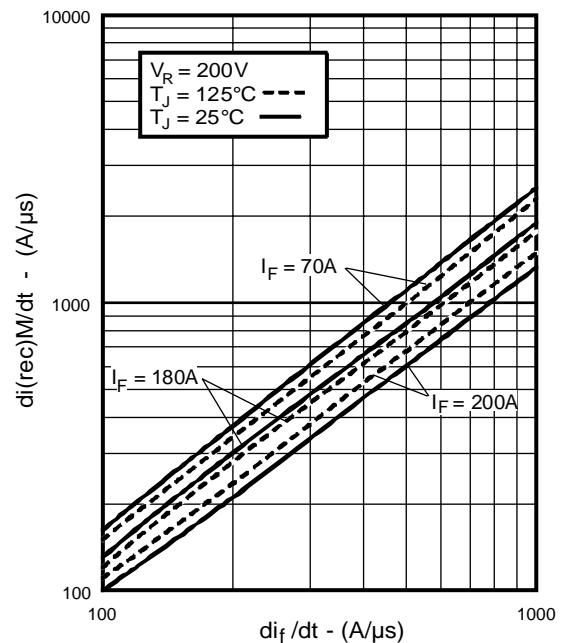
**Fig. 5 - Typical Reverse Recovery vs.  $di_f/dt$**



**Fig. 6 - Typical Recovery Current vs.  $di_f/dt$**

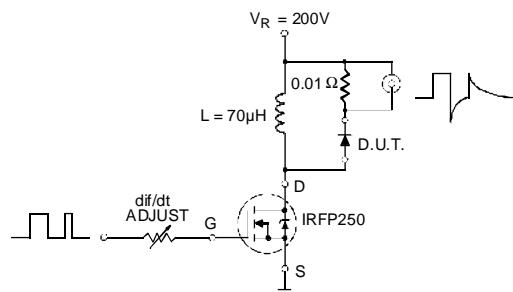


**Fig. 7 - Typical Stored Charge vs.  $di_f/dt$**

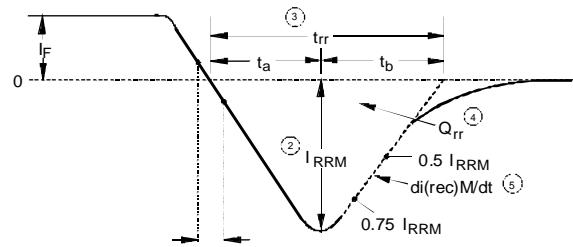


**Fig. 8 - Typical  $dI_{(rec)}/dt$  vs.  $di_f/dt$**

REVERSE RECOVERY CIRCUIT

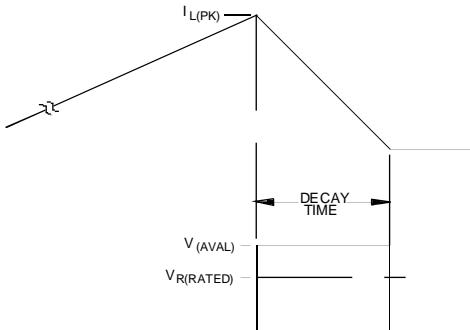
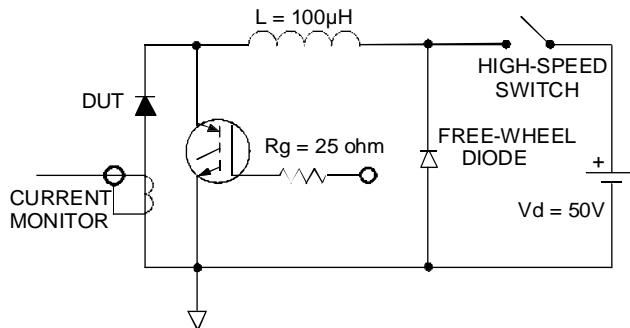


**Fig. 9 - Reverse Recovery Parameter Test Circuit**



1.  $\frac{di}{dt}$  - Rate of change of current through zero crossing
  2.  $I_{RRM}$  - Peak reverse recovery current
  3.  $t_{rr}$  - Reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through  $0.75 I_{RRM}$  and  $0.50 I_{RRM}$  extrapolated to zero current
  4.  $Q_{rr}$  - Area under curve defined by  $t_{rr}$  and  $I_{RRM}$
  5.  $\frac{di_{(rec)}M}{dt}$  - Peak rate of change of current during  $t_b$  portion of  $t_{rr}$
- $$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

**Fig. 10 - Reverse Recovery Waveform and Definitions**



**Fig. 11 - Avalanche Test Circuit and Waveforms**

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